## Oral Session

Oral Session								
Keynote/Invited	Presentation	Presentatio n date	Time to start	Time to	Account: First	Account: Account: FAMILY	Account: Affiliation	Abstract title
				finish	name	Middle name NAME		
Chairpersons:Dr. T		-						
Invited	B-1-I27-001	27 Sep.	13:30	13:50	Roy	G. GORDON	Harvard University	Vapor Deposition of Materials for Semiconductors
	B-1-O27-002	27 Sep.	13:50	14:05	Kohei	SHIMA	student	High Density Nucleation to Realize Ultra Thin and Continuous CVD-Cu Film Using Ruthenium Glue Layer Applied to Highly Reliable ULSIs
	B-1-O27-003	27 Sep.	14:05	14:20	Brett	Cameron Johnson	Japan Atomic Energy Agency	Dopant activation by solid phase epitaxy in silicon and germanium
	B-1-O27-004	27 Sep.	14:20	14:35	Daniel	MORARU	Shizuoka University	Experimental and ab initio Study of Donor State Deepening in Nanoscale SOI-MOSFETs
	B-1-O27-005	27 Sep.	14:35	14:50	Koya	HOZAKI	Nagoya University	In situ Sb doping in Ge1-xSnx Epitaxial Layers with High Sn Contents
Coffee Break		27 Sep.	14:50	15:15				
Chairpersons:Prof.	Shigeaki Zaima (N	Vagoya Univ.,	Japan)					
vited	B-1-I27-006	27 Sep.	15:15	15:35	Kuan-Neng	CHEN	National Chiao Tung University	Material Analyses and Morphology Investigations of Cu-Based Bonding Technology for 3D Integration
	B-1-O27-007	27 Sep.	15:35	15:50	Vladimir	POBORCHII	National Institute of Advanced Industrial Science and Technology	Enhancement of the Strained Si Doublet Phonon Raman Signal Using Radial Polarization of Light and High Numerical Aperture Lens
	B-1-O27-008	27 Sep.	15:50	16:05	Leonid	BOLOTOV	University of Tsukuba	Built-in Potential Mapping of Silicon Field Effect Transistor Cross Sections by Multimode Scanning Probe Microscopy
	B-1-O27-009	27 Sep.	16:05	16:20	Naoki	TSUNEKAWA	Nagoya University	Temporal Changes of Charge Distribution in High Density Self-aligned Si-based Quantum Dots as Evaluated by AFM/KFM
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	Masaaki Niwa (Ur	<u>,</u>		10.20				
vited	B-1-I27-010	27 Sep.	16:30	16:50	Yoshiyuki	YAMASHITA	National Institute for Materials Science and Kyusyu University	ICMRS_invited_Yamashita
vited	B-1-027-011	27 Sep. 27 Sep.	16:50	17:05	Akio	OHTA	Hiroshima University	XPS Study of Energy Band Alignment between Hf-La Oxides and Si(100)
	B-1-027-011 B-1-027-012	27 Sep. 27 Sep.	17:05	17:03	Jun	CHEN	National Institute for Materials Science	Observation of Leakage Sites in High-k Gate Stack by Using an Electron-Beam-Induced Current Technique
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	B-1-O27-013	27 Sep.	17:20	17:35	Matthieu	PY	Kyoto University, Quantum Science and Engineering Center	Low Energy Full Spectrum Time of Flight-SIMS for accurate depth profiling of advanced dielectric/gate stack materials
-	Yee-Chia Yeo (Na				D			
vited	B-1-I28-001	28 Sep.	9:00	9:20	Roger	LOO	imec	Epitaxial Growth in advanced SiGe and Ge MOS devices: challenges and solutions
	B-1-O28-002	28 Sep.	9:20	9:35	Mohammad		Kyushu University	Formation of Germanium Epitaxial Layer on Insulator Using Nanostructured Rapid-Melting-Grown Template
	B-1-O28-003	28 Sep.	9:35	9:50	Takanori	ASANO	Nagoya Univ.	Epitaxial Growth of Ge1-xSnx Layers on (110)-oriented Si and Ge Substrates
	B-1-O28-004	28 Sep.	9:50	10:05	Ryo	MATSUMURA	Kyushu University	Si Segregation Behavior in Giant SiGe Stripes on Insulator during Rapid-Melting-Growth
	B-1-O28-005	28 Sep.	10:05	10:20	Takayoshi	SHIMURA	Graduate School of Engineering, Osaka University	Rapid Melt Growth of Fully Relaxed SiGe Layers with High Ge Concentration on Silicon-on-Insulator Substrates
offee Break		28 Sep.	10:20	10:30				
hairpersons:Prof.	Horng-Chih Lin (1	National Chiad	o Tung Univ.,	Taiwan)				
vited	B-1-I28-006	28 Sep.	10:30	10:50	Edward Yi	CHANG	Nattional Chiao Tung University,	The Growth of III-V and Ge on Si for High-Speed and Low-Power Logic Device Application (Invited)
vited	B-1-I28-007		10:50	11:10	Yee-Chia	YEO	National University of Singapore	New Device Structures and Materials for Nano-CMOS
	B-1-O28-008	28 Sep.	11:10	11:25	Hirotaka	YOSHIOKA	Kyushu University	Suppression of Fermi-level pinning at bcc-metal/Ge(111) interfaces
	B-1-O28-009	28 Sep.	11:25	11:40	Hideki	MURAKAMI	Hiroshima University	Photoemission Study of GeO2/Ge Structure Formed by Thermal Oxidation
	B-1-O28-010	28 Sep.	11:40	11:55	shigehisa	SHIBAYAMA	Nagoya University	Thermal Oxidation Mechanism of Ge through Al2O3 Layer Formed on Ge Substrate
	B-1-O28-011	28 Sep.	11:55	12:10	Keisuke	CHIKARAISHI	Graduate School of Engineering, Osaka university	Effective Work Function Control of MIPS/high-k Gate Stacks by Al-incorporation and in situ Low-pressure Oxidation of TiN Surface
	B-1-O28-012	28 Sep.	12:10	12:25	Kuniyuki	KAKUSHIMA	Tokyo Institute of Technology	Interface Controlled Stacked Ni silicidation Process with Schottky Barrier Height Controllability
ınch	B-1-020-012	28 Sep.	12:25	13:30	Kulliyuki		Tokyo institute of Technology	internate controlled blacked for sinekauton frocess with benotiky burlet freight controllability
	Shigeaki Zaima (N	<u>,</u>		15.50				
*		<u> </u>		12.50	Won Vouna	II NC	Donahu HiTak	Nevel Measurement Method without Self Hesting Effect in LDMOS
vited	B-1-I28-013	28 Sep.	13:30	13:50	Won-Young	JUNG	Dongbu HiTek	Novel Measurement Method without Self Heating Effect in LDMOS
	B-1-O28-014	28 Sep.	13:50	14:05	Noriyuki	TAOKA	Nagoya University	Importance of Si Bandbending at Zero Bias Condition for Schottky Barrier Height Control at Metal/Si Interfaces with Ultra-thin Al2O3 Layer
	B-1-O28-015	28 Sep.	14:05	14:20	Kenji	OHMORI	University of Tsukuba	Characterization of High-Frequency Noise in MOSFETs
	B-1-O28-016	28 Sep.	14:20	14:35	Horng-Chih	LIN	National Chiao Tung University	Using Si Nanocrystal-Embedded Gate Nitride to Improve Endurance Characteristics of Devices with Suspended Poly-Si Nanowire Channels
	B-1-O28-017	28 Sep.	14:35	14:50	Tzu-I	TSAI	National Chiao Tung University	Low-Operating-Voltage Poly-Si Thin-Film Transistor Technology for RF Applications
	B-1-O28-018	28 Sep.	14:50	15:05	Ko-Hui	LEE	National Chiao Tung University	A Simple Method for Fabricating Sublithographic Short-Channel Tri-Gated Nanowire Poly-Si TFTs
	B-1-O28-019	28 Sep.	15:05	15:20	Shunsuke	ASABA	Graduate School of Engineering, Nagoya University	Electrical Properties of Epitaxially Grown p+-Ge1-xSnx/n-Ge Diodes
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	B-1-P26-001	26 Sep.	16:30	18:30	Young	Kyun LEE	Pusan National University	Effects of Ceria Oxide-Mixed Abrasive Slurry on the Tetra-Ethyl Ortho-Silicate Oxide Chemical Mechanical Polishing for Planarization of Inter-Layer Dielectric film in the Multilevel Interco
	B-1-P26-002	26 Sep.	16:30	18:30	Xiao	na LI	Dalian University of Technology	High performance Cu(NiNb) films for Barrierless Metallization
	B-1-P26-003	26 Sep.	16:30	18:30	Leonid	BOLOTOV	University of Tsukuba	Nanoscale characterization of silicon-on-insulator nanowires by multimode scanning probe microscopy
	B-1-P26-004	26 Sep.	16:30	18:30	Vladimir	POBORCHII	National Institute of Advanced Industrial Science and Technology	UV Absorption and Raman Enhancement in a Few Nanometer Thick Si-on-Insulator
	B-1-P26-005	26 Sep.	16:30	18:30	sungjin	PARK	National Institute of Advanced Industrial Science and Technology (A	Al Carrier density depth profiling at shallow surface of phosphorus doped crystalline silicon using High Resolution Electron Energy Loss Spectroscopy (HREELS)
	B-1-P26-006	26 Sep.	16:30	18:30	Yuji	IKEDA	Kyoto University	Analysis of Local Electric Conductivities for Si Nanowire Models
	B-1-P26-007	26 Sep.	16:30	18:30	Nobuya	MORI	Osaka University	Disorder-Induced Enhancement of Impact Ionization Rate in Silicon Nanodots
	B-1-P26-008	26 Sep.	16:30	18:30	Masato	SENAMI	Kyoto University	Local Quantity Analysis of Nanosize Electronics and spintronics Material
	B-1-P26-009	26 Sep.	16:30	18:30	Ming Ho		National Tsing Hua University	Improvement of electrical properties via cyclic and surface D20 plasma treatments on Hf02/L a203/Ge MOS devices in atomic layer deposition process

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27 Sep.14:5015:155. Shigeaki Zaima (Nagoya Univ., Japan)										
	geaki Zailia (1 -1-I27-006		-	15:35	Kuan-Neng		CHEN	National Chiao Tung University	Material Analyses and Morphology Investigations of Cu-Based Bonding Technology for 3D Integration	
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	-1-027-007	<u>^</u>	15:50	16:05	Leonid		BOLOTOV	University of Tsukuba		
	-1-027-008	27 Sep. 27 Sep.	16:05	16:20	Naoki			Nagoya University	Built-in Potential Mapping of Silicon Field Effect Transistor Cross Sections by Multimode Scanning Probe Microscopy   Temporal Changes of Charge Distribution in High Density Self-aligned Si-based Quantum Dots as Evaluated by AFM/KFM	
[E	-1-027-009	*			INAUKI		ISUNEKAWA	Nagoya University	Temporal Changes of Charge Distribution in Figh Density Sen-anglied Si-based Quantum Dots as Evaluated by AFM/KFW	
27 Sep.16:2016:30f. Masaaki Niwa (Univ. of Tsukuba, Japan)										
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	-1-027-011	27 Sep. 27 Sep.	17:05	17:20	Jun			National Institute for Materials Science	Observation of Leakage Sites in High-k Gate Stack by Using an Electron-Beam-Induced Current Technique	
	-1-027-012	27 Sep. 27 Sep.	17:03	17:20	Matthieu			Kyoto University, Quantum Science and Engineering Center	Low Energy Full Spectrum Time of Flight-SIMS for accurate depth profiling of advanced dielectric/gate stack materials	
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	-1-028-001	28 Sep. 28 Sep.	9:00	9:20	Roger Mohammad	+		Kyushu University	Formation of Germanium Epitaxial Layer on Insulator Using Nanostructured Rapid-Melting-Grown Template	
	-1-028-002	28 Sep. 28 Sep.	9:35	9:50	Takanori			Nagoya Univ.	Epitaxial Growth of Ge1-xSnx Layers on (110)-oriented Si and Ge Substrates	
	-1-028-003	28 Sep. 28 Sep.	9:50	10:05	Ryo			Kyushu University	Si Segregation Behavior in Giant SiGe Stripes on Insulator during Rapid-Melting-Growth	
	-1-028-004	28 Sep. 28 Sep.	10:05	10:00	Takayoshi			Graduate School of Engineering, Osaka University	Rapid Melt Growth of Fully Relaxed SiGe Layers with High Ge Concentration on Silicon-on-Insulator Substrates	
E	-1-028-003	28 Sep. 28 Sep.	10:03	10:20	Такауовш		SHIMUKA	Graduate School of Engineering, Osaka University	Rapid Meit Growth of Fully Relaxed Side Layers with High Ge Concentration on Sincon-on-Insulator Substrates	
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	-1-I28-006	28 Sep.	10:30	10:50	Edward Yi		CHANG	Nattional Chiao Tung University,	The Growth of III-V and Ge on Si for High-Speed and Low-Power Logic Device Application (Invited)	
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	-1-028-011	28 Sep.	12:10	12:10	Kuniyuki			Tokyo Institute of Technology	Interface Controlled Stacked Ni silicidation Process with Schottky Barrier Height Controllability	
	-1-020-012	28 Sep.	12:25	13:30	Kulliyuki		RAROSIIIWA	Tokyo institute of Technology	Interface Controlled Stacked IV sincidation Process with Schottky Darner Height Controllability	
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	-1-I28-013	28 Sep.	13:30	13:50	Won-Young		JUNG	Dongbu HiTek	Novel Measurement Method without Self Heating Effect in LDMOS	
	-1-028-014	28 Sep.	13:50	14:05	Noriyuki			Nagoya University	Importance of Si Bandbending at Zero Bias Condition for Schottky Barrier Height Control at Metal/Si Interfaces with Ultra-thin Al2O3 Layer	
	-1-028-014	28 Sep.	14:05	14:20	Kenji			University of Tsukuba	Characterization of High-Frequency Noise in MOSFETs	
	-1-028-015	28 Sep.	14:20	14:35	Horng-Chih	1		National Chiao Tung University	Using Si Nanocrystal-Embedded Gate Nitride to Improve Endurance Characteristics of Devices with Suspended Poly-Si Nanowire Channels	
	-1-028-010	28 Sep. 28 Sep.	14:35	14:50	Tzu-I	1		National Chiao Tung University	Low-Operating-Voltage Poly-Si Thin-Film Transistor Technology for RF Applications	
	-1-028-017	28 Sep.	14:50	15:05	Ko-Hui	1		National Chiao Tung University	A Simple Method for Fabricating Sublithographic Short-Channel Tri-Gated Nanowire Poly-Si TFTs	
	-1-028-019	28 Sep.	15:05	15:20	Shunsuke			Graduate School of Engineering, Nagoya University	Electrical Properties of Epitaxially Grown p+-Ge1-xSnx/n-Ge Diodes	
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	-1-P26-003	26 Sep.	16:30	18:30	Leonid		BOLOTOV	University of Tsukuba	Nanoscale characterization of silicon-on-insulator nanowires by multimode scanning probe microscopy	
	-1-P26-004	26 Sep.	16:30	18:30	Vladimir			National Institute of Advanced Industrial Science and Technology	UV Absorption and Raman Enhancement in a Few Nanometer Thick Si-on-Insulator	
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_	-1-P26-009	26 Sep.	16:30	18:30	Ming-Ho			National Tsing Hua University	Improvement of electrical properties via cyclic and surface D2O plasma treatments on HfO2/La2O3/Ge MOS devices in atomic layer deposition process	
	-1-P26-010	26 Sep.	16:30	18:30	Pi-Chun		JUAN	Ming Chi University of Technology	The Effects of Post-Deposition and Post-Metallization Annealing on the Physical and Electrical Properties of Metal-Gate (ZrN)/High-k Dielectric (LaZrO)/Si MIS Structures	
	-1-P26-011	26 Sep.	16:30	18:30	Katsumasa		KAMIYA	University of Tsukuba	Work Functions of Curved Aluminum Surfaces	
	-1-P26-012	26 Sep.	16:30	18:30	Ryo			Kyushu University	Formation of N-Type Ge-on-Insulator through P-Implantation and Rapid-Melting Growth	
	-1-P26-013	26 Sep.	16:30	18:30	Yu-Ting			National Central University	Thermal stability of supersaturated carbon incorporation in silicon	
E	-1-P26-014	26 Sep.	16:30	18:30	Amal		CHABLI	CEA-Leti	New generation state-of-the-art Auger Nanoprobes for the analysis of Si/SiGe superlattice heterostructures	